

**Electrical Characteristics @ T<sub>j</sub> = 25°C (Unless Otherwise Specified)**

	Parameter	Min	Typ	Max	Units	Test Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	500	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0mA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	—	0.78	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1.0mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-State Resistance	—	—	0.85	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.4A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	4.7	—	—	S (r)	V <sub>DS</sub> > 15V, I <sub>DS</sub> = 4.4A ④
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	—	25	μA	V <sub>DS</sub> = 400V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 400V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	—	100	nA	V <sub>GS</sub> = 20V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	—	-100		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	—	—	68.5	nC	V <sub>GS</sub> = 10V, I <sub>D</sub> = 7.0A V <sub>DS</sub> = 250V
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	12.5		
Q <sub>gd</sub>	Gate-to-Drain ('Miller') Charge	—	—	42.4		
t <sub>d(on)</sub>	Turn-On Delay Time	—	—	21	ns	V <sub>DD</sub> = 250V, I <sub>D</sub> = 7.0A, R <sub>G</sub> = 9.1Ω
t <sub>r</sub>	Rise Time	—	—	73		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	—	72		
t <sub>f</sub>	Fall Time	—	—	51		
L <sub>S</sub> + L <sub>D</sub>	Total Inductance	—	6.8	—	nH	Measured from drain lead (6mm/0.25in. from package) to source lead (6mm/0.25in. from package)
C <sub>iss</sub>	Input Capacitance	—	1300	—	pF	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	310	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	120	—		

**Source-Drain Diode Ratings and Characteristics**

	Parameter	Min	Typ	Max	Units	Test Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	7.0	A	T <sub>j</sub> = 25°C, I <sub>S</sub> = 7.0A, V <sub>GS</sub> = 0V ④
I <sub>SM</sub>	Pulse Source Current (Body Diode) ①	—	—	28		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.5	V	T <sub>j</sub> = 25°C, I <sub>F</sub> = 7.0A, di/dt ≤ 100A/μs V <sub>DD</sub> ≤ 50V ④
t <sub>rr</sub>	Reverse Recovery Time	—	—	700	nS	
Q <sub>RR</sub>	Reverse Recovery Charge	—	—	8.9	μC	
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L <sub>S</sub> + L <sub>D</sub> .				

**Thermal Resistance**

	Parameter	Min	Typ	Max	Units	Test Conditions
R <sub>thJC</sub>	Junction-to-Case	—	—	1.25	°C/W	
R <sub>thCS</sub>	Case-to-sink	—	0.21	—		
R <sub>thJA</sub>	Junction-to-Ambient	—	—	80		Typical socket mount

**Note:** Corresponding Spice and Saber models are available on the G&S Website.

For footnotes refer to the last page

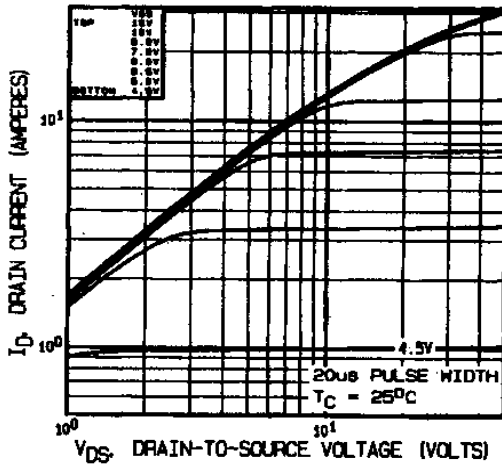


Fig 1. Typical Output Characteristics

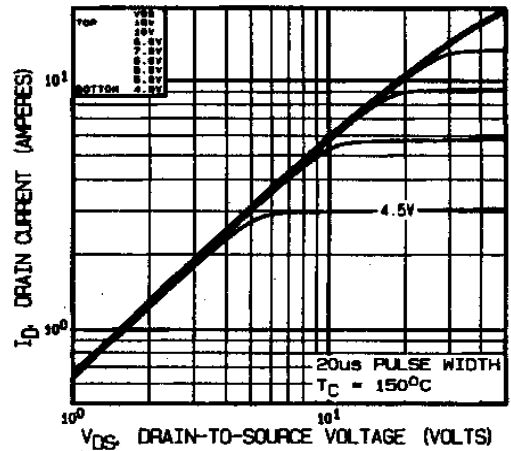


Fig 2. Typical Output Characteristics

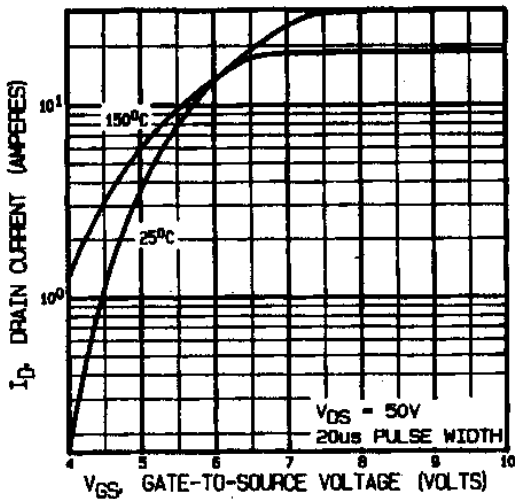


Fig 3. Typical Transfer Characteristics

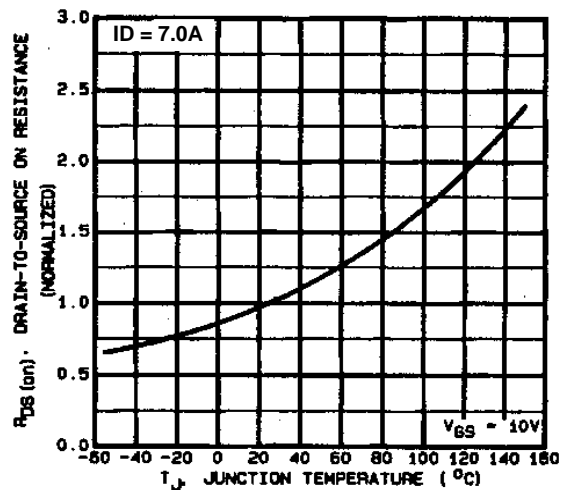


Fig 4. Normalized On-Resistance  
Vs. Temperature

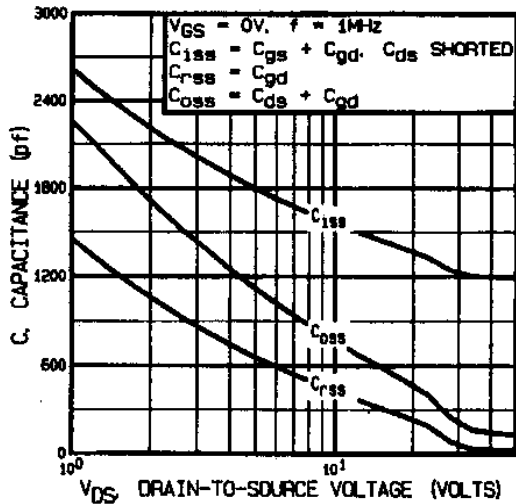


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

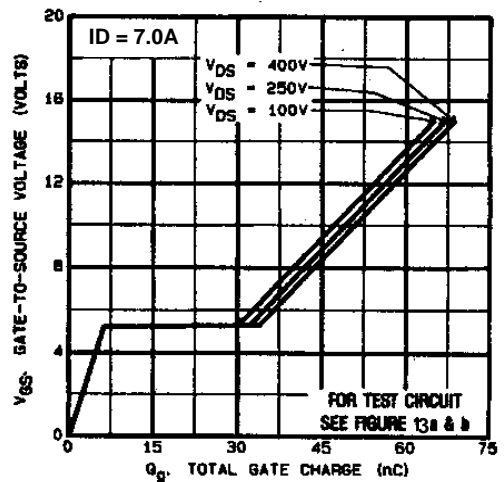


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

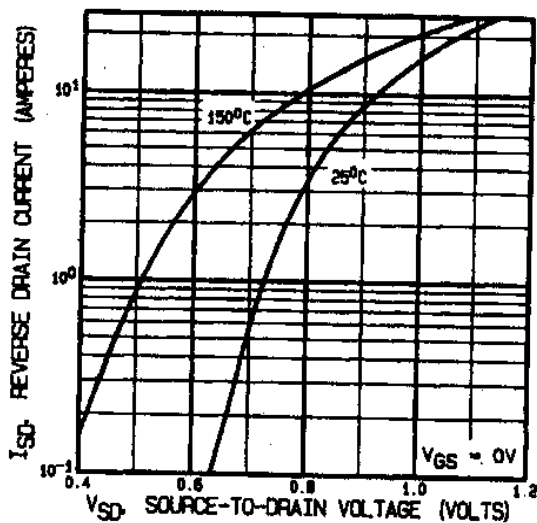


Fig 7. Typical Source-Drain Diode Forward Voltage

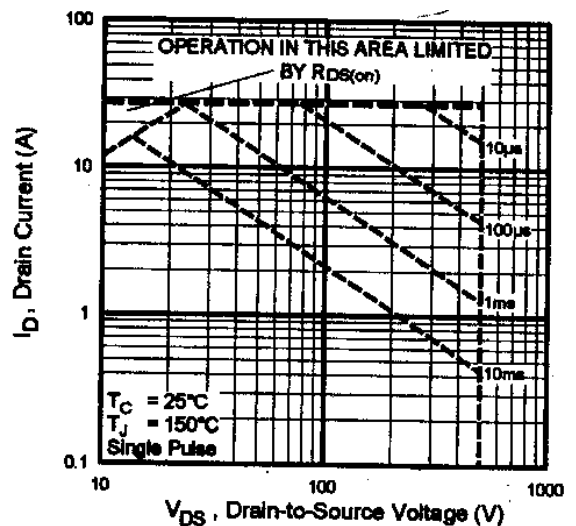
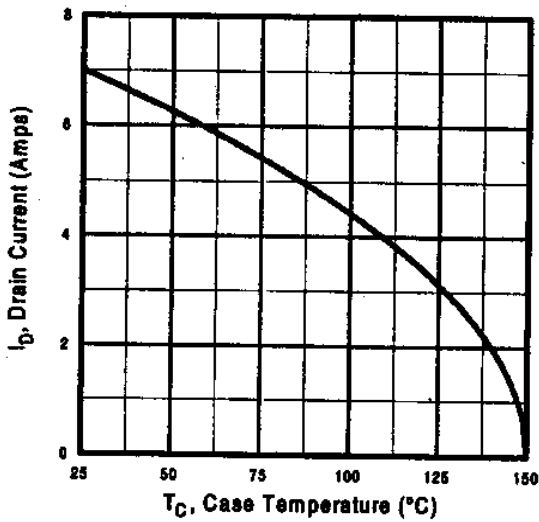
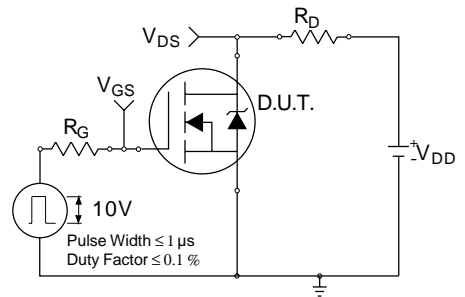


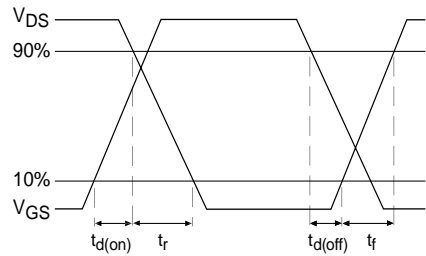
Fig 8. Maximum Safe Operating Area



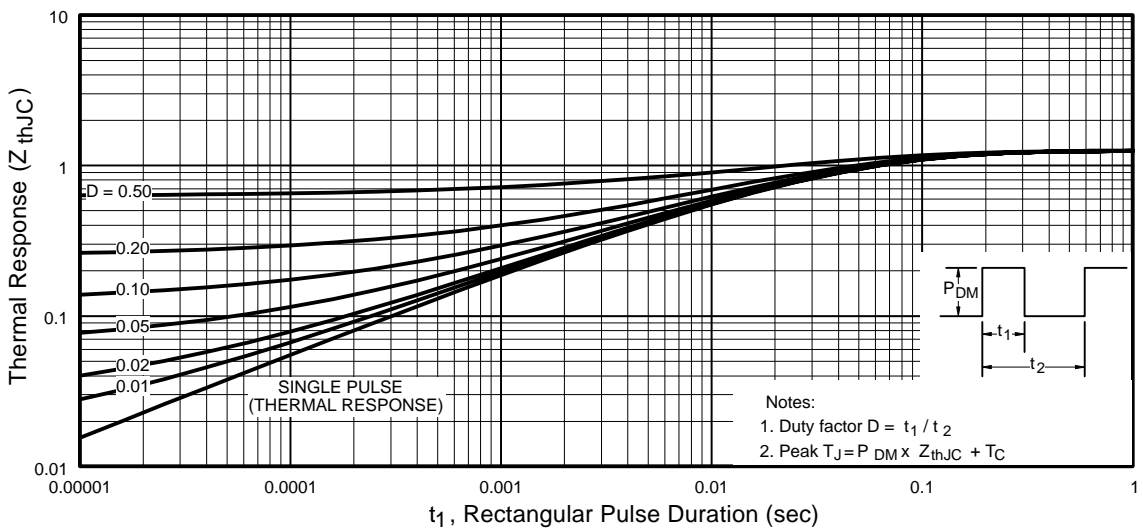
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



**Fig 10b.** Switching Time Waveforms



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

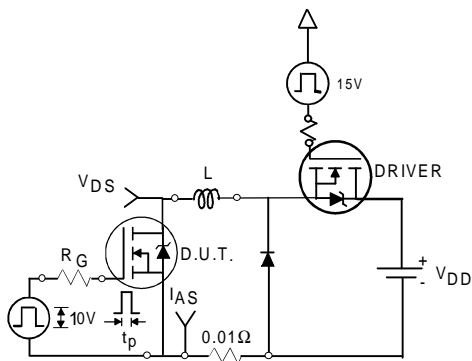


Fig 12a. Unclamped Inductive Test Circuit

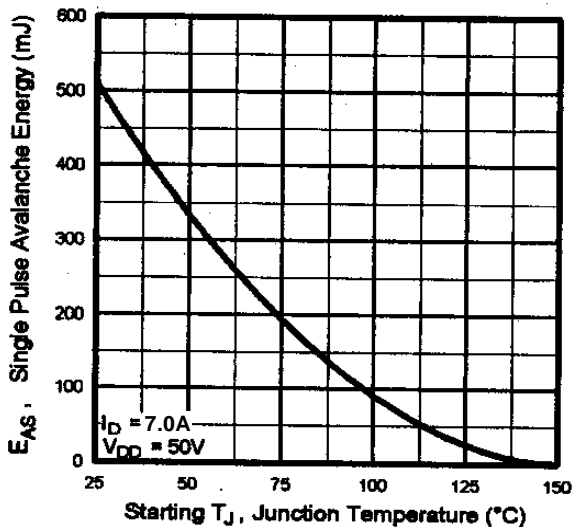


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

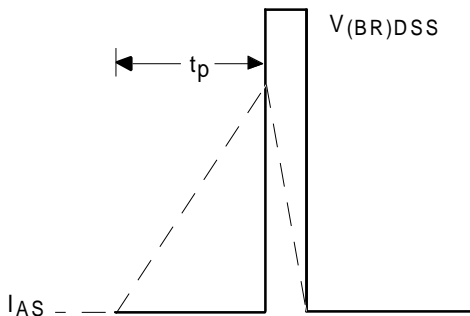


Fig 12b. Unclamped Inductive Waveforms

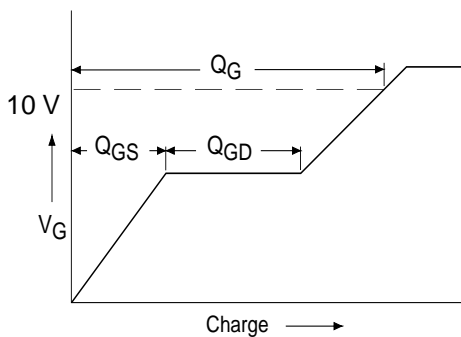


Fig 13a. Basic Gate Charge Waveform

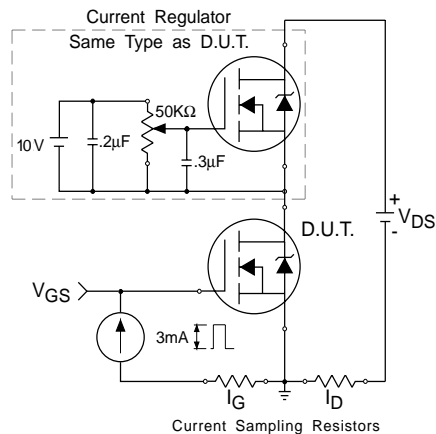
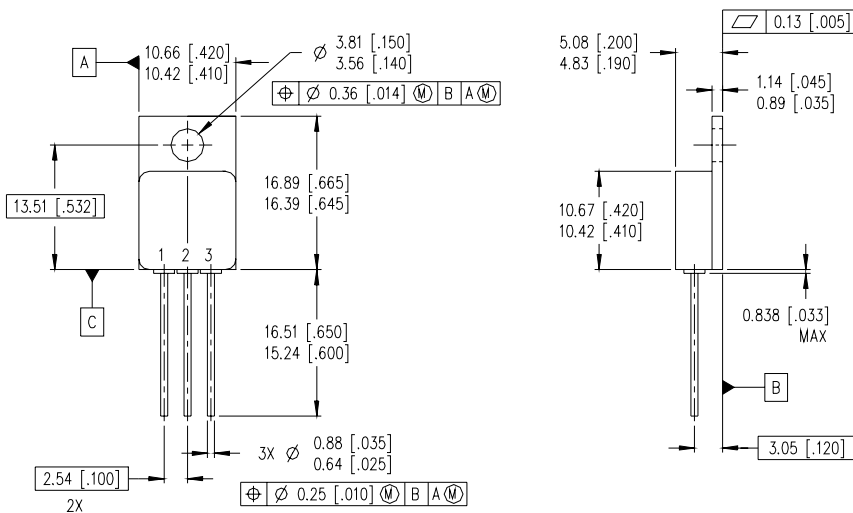


Fig 13b. Gate Charge Test Circuit

## Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ②  $V_{DD} = 50V$ , starting  $T_J = 25^\circ C$ ,  $L = 20mH$   
Peak  $I_L = 7.0A$ ,  $V_{GS} = 10V$
- ③  $I_{SD} \leq 7.0A$ ,  $di/dt \leq 100A/\mu s$ ,  
 $V_{DD} \leq 500V$ ,  $T_J \leq 150^\circ C$
- ④ Pulse width  $\leq 300 \mu s$ ; Duty Cycle  $\leq 2\%$

## Case Outline and Dimensions — TO-257AA



### NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-257AA.

### LEGEND

D - DRAIN  
S - SOURCE  
G - GATE

